

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		S15 and ((implant\$4 and (dual double second two)	USPAT	OR	OFF	2005/06/07 11:21
L1	0	krishnaswamy-ramkumar.in.	USPAT	OR	OFF	2005/06/07 11:23
L2	0	("krishnaswamy-ramkumar.in.").PN.	USPAT; USOCR	OR	OFF	2005/06/07 11:23
L3	1	krishnaswamy-ramkumar.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/07 11:24
L4	36	ramkumar-krishnaswamy.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/07 11:33
L5	5	bamnolker-hanna.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/07 11:33
L6	29	("3430109" "3585714" "4256514" "4639288" "4851361" "4916513" "4946800" "4965221" "4992390" "5151381" "5296094" "5334861" "5393679" "5431778" "5443998" "5447884" "5498577" "5672521" "5679483" "5688701" "5702988" "5739056" "5750428" "5792680" "5795803" "5869385" "5900658").PN. OR ("6555484").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/07 12:35
L7	1480	(438/229,514,519,522,911,920, 981).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/07 12:42
L8	137	L7 and ((screen\$3 sacrificial) with oxid\$5)	USPAT	OR	OFF	2005/06/07 12:43
L9	86	L8 and ((implant\$5 dop\$3) with (dual double two twice second))	USPAT	OR	OFF	2005/06/07 12:43
L10	11	L9 and (anneal with (dual double twice second two))	USPAT	OR	OFF	2005/06/07 12:43
L11	97959	("438").CLAS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/07 12:42
L12	3134	L11 and ((screen\$3 sacrificial) with oxid\$5)	USPAT	OR	OFF	2005/06/07 12:43
L13	1609	L12 and ((implant\$5 dop\$3) with (dual double two twice second))	USPAT	OR	OFF	2005/06/07 12:43

L14	101	L13 and (anneal with (dual double twice second two))	USPAT	OR	OFF	2005/06/07 12:46
L15	100	L14 and silicon	USPAT	OR	OFF	2005/06/07 12:47
L16	42	L15 and "silicon oxide"	USPAT	OR	OFF	2005/06/07 12:47
S1	307230	EEPROM EPROM ROM "read only memory" flash non-volatile	USPAT	OR	OFF	2005/05/26 14:56
S2	49796	S1 and (implant\$5 impurity ion dop\$3)	USPAT	OR	OFF	2005/05/26 14:57
S3	18059	S2 and (anneal thermal RTA drive-in)	USPAT	OR	OFF	2005/05/26 14:58
S5	5220	S3 and (tunnel 100A floating F-N fowler-nordheim)	USPAT	OR	OFF	2005/05/26 15:07
S8	1556	S5 and ((multiple with layers) (multiple with dielectric) (multiple with oxide) (plurality with layers) (plurality with dielectric) (plurality with oxide))	USPAT	OR	OFF	2005/05/26 15:10
S9	1460	S8 and silicon	USPAT	OR	OFF	2005/05/26 15:24
S10	115	(438/529 438/530) and (EEPROM EPROM flash floating non-volatile)	USPAT	OR	OFF	2005/05/26 15:45
S11	124	(438/529 438/530) and (EEPROM EPROM flash floating non-volatile tunnel)	USPAT	OR	OFF	2005/05/26 17:14
S12	0	438/257,263,264	USPAT	OR	OFF	2005/05/26 17:16
S13	355	438/257-267	USPAT	OR	OFF	2005/05/26 17:16
S14	25	438/257-264	USPAT	OR	OFF	2005/05/26 17:17
S15	2728	(438/257-264).CCLS.	USPAT; USOCR	OR	OFF	2005/05/26 17:17
S16	1873	S15 and (implant\$4 and (dual double second two))	USPAT	OR	OFF	2005/05/26 17:43
S17	264	S16 and (anneal and (dual double twice two second))	USPAT	OR	OFF	2005/05/26 17:44
S18	463	(438/529-530).CCLS.	USPAT; USOCR	OR	OFF	2005/05/26 17:19
S19	0	("L7and(EEPROMEPROMflashfloatin gnon-volatiletunnel)").PN.	USPAT; USOCR	OR	OFF	2005/05/26 17:19
S20	72	S18 and (EEPROM EPROM flash floating non-volatile tunnel)	USPAT	OR	OFF	2005/05/26 17:20
S21	832	S15 and (implant\$4 with (dual double second two))	USPAT	OR	OFF	2005/05/26 17:43
S22	22	S21 and (anneal with (dual double twice two second))	USPAT	OR	OFF	2005/05/26 17:43
S24	223	S17 and (silicon with oxide)	USPAT	OR	OFF	2005/05/26 17:44
S25	3275	(257/314-326).CCLS.	USPAT; USOCR	OR	OFF	2005/06/02 15:44

S26	4289	(257/314-326).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/02 15:44
S27	0	("L2and(implant\$5same(dualdouble secondtwo))").PN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/02 15:45
S28	1945	S26 and (implant\$5 same (dual double second two))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/02 15:45
S29	360	S28 and (anneal\$3 same (dual double twice two second))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/02 15:46
S30	986	S28 and (tunnel same (oxid\$5)) and silicon	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/02 15:47
S31	168	S29 and (tunnel same (oxid\$5)) and silicon	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 11:43
S32	209	(438/914,923).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 11:44
S33	9	S32 and (anneal with (dual double twice two second))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 12:02
S34	0	chang-hun-han.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 12:04
S35	32	sakamoto-masaru.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 15:31
S36	0	dong-oog-kim.IN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 12:04
S37	378	(438/546).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 15:37

S38	369	(438/530).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 15:34
S39	3	S37 and S38	USPAT	OR	OFF	2005/06/03 15:34
S40	3	S37 and (anneal with (dual double twice two second))	USPAT	OR	OFF	2005/06/03 15:35
S41	3	S37 and (anneal with (dual double twice two second))	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 15:36
S42	154	S37 and silicon	USPAT	OR	OFF	2005/06/03 15:37
S43	4	S42 and ((screen\$3 sacrificial) near5 (oxid\$5))	USPAT	OR	OFF	2005/06/03 15:40
S44	744	(438/530,546).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 15:41
S45	1630	(438/530,546,550,766,770).CCLS.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 15:41
S46	0	("L9andsiliconwithoxide").PN.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2005/06/03 15:42
S47	882	S45 and silicon with oxide	USPAT	OR	OFF	2005/06/03 15:42
S48	93	S47 and ((screen\$3 sacrificial) near5 oxid\$5)	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2005/06/03 15:43